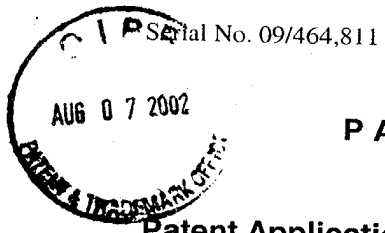


#13/B
8/29/02
Mullis



IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

Patent Application

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8-20-02

Inventor(s): **Shao et al.**
Case: **1-10-3**
Serial No.: **09/464,811**
Filing Date: **December 17, 1999**
Examiner: **Lourdes Cruz**
Title: **Integration of Low Dielectric Material in Semiconductor Circuit Structures**

Group Art Unit: **2827**

Mary Carter
Printed name of person mailing paper or fee
Mary Carter
Signature of person mailing paper or fee

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D. C. 20231

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Amendment Under 37 C.F.R. §1.111

SIR:

In response to the office action of April 5, 2002 please amend the application as follows:

IN THE SPECIFICATION

✓ At page 1, change the title to "Integration of Low K Dielectric Material in Semiconductor Circuit Structures."

IN THE CLAIMS

Please amend the claims as follows:

B1

27. A method for fabricating an integrated circuit structure comprising:
forming multiple levels of conductor lines over one another with
some of the levels separated from one another by a layer of first insulative
material;